

FDS4488

30V N-Channel PowerTrench[®] MOSFET

General Description

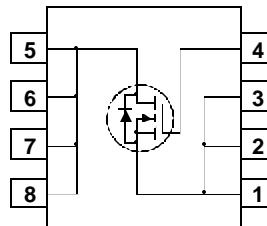
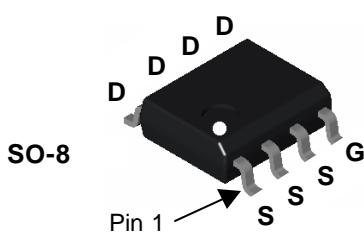
This NChannel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain superior switching performance. These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.

Applications

- DC/DC converter
- Load switch
- Motor drives

Features

- 7.9 A, 30 V. $R_{DS(ON)} = 22 \text{ m}\Omega$ @ $V_{GS} = 10 \text{ V}$
 $R_{DS(ON)} = 30 \text{ m}\Omega$ @ $V_{GS} = 4.5 \text{ V}$
- Low gate charge (9.5 nC typical)
- High performance trench technology for extremely low $R_{DS(ON)}$
- High power and current handling capability



Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain-Source Voltage	30	V
V_{GSS}	Gate-Source Voltage	± 25	V
I_D	Drain Current – Continuous (Note 1a)	7.9	A
	– Pulsed	40	
P_D	Power Dissipation for Single Operation (Note 1a)	2.5	W
	(Note 1b)	1.2	
	(Note 1c)	1.0	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +175	°C

Thermal Characteristics

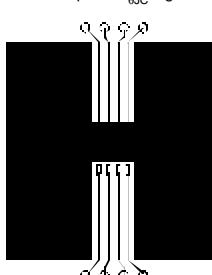
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	50	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	25	

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDS4488	FDS4488	13"	12mm	2500 units

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units	
Off Characteristics							
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	30			V	
$\Delta \text{BV}_{\text{DSS}}$ ΔT_J	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C		21		mV°C	
I_{SS}	Zero Gate Voltage Drain Current	$V_{\text{DS}} = 24 \text{ V}$, $V_{\text{GS}} = 0 \text{ V}$		1		μA	
I_{GSSF}	Gate-Body Leakage, Forward	$V_{\text{GS}} = 25 \text{ V}$, $V_{\text{DS}} = 0 \text{ V}$		100		nA	
I_{GSSR}	Gate-Body Leakage, Reverse	$V_{\text{GS}} = -25 \text{ V}$, $V_{\text{DS}} = 0 \text{ V}$		-100		nA	
On Characteristics (Note 2)							
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{\text{DS}} = V_{\text{GS}}$, $I_D = 250 \mu\text{A}$	1	1.8	3	V	
$\Delta V_{\text{GS(th)}}$ ΔT_J	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C		-6		mV°C	
$R_{\text{DS(on)}}$	Static Drain-Source On-Resistance	$V_{\text{GS}} = 10 \text{ V}$, $I_D = 7.9 \text{ A}$ $V_{\text{GS}} = 4.5 \text{ V}$, $I_D = 6.8 \text{ A}$ $V_{\text{GS}} = 10 \text{ V}$, $I_D = 7.9 \text{ A}$, $T_J = 125^\circ\text{C}$	15 21 22	22 30 35		$\text{m}\Omega$	
$I_{\text{D(on)}}$	On-State Drain Current	$V_{\text{GS}} = 10 \text{ V}$, $V_{\text{DS}} = 5 \text{ V}$	20			A	
g_{FS}	Forward Transconductance	$V_{\text{DS}} = 10 \text{ V}$, $I_D = 7.9 \text{ A}$		24		S	
Dynamic Characteristics							
C_{iss}	Input Capacitance	$V_{\text{DS}} = 15 \text{ V}$, $V_{\text{GS}} = 0 \text{ V}$, $f = 1.0 \text{ MHz}$		927		pF	
C_{oss}	Output Capacitance			241		pF	
C_{rss}	Reverse Transfer Capacitance			97		pF	
Switching Characteristics (Note 2)							
$t_{\text{d(on)}}$	Turn-On Delay Time	$V_{\text{DD}} = 15 \text{ V}$, $I_D = 1 \text{ A}$, $V_{\text{GS}} = 10 \text{ V}$, $R_{\text{GEN}} = 6 \Omega$		7.4	15	ns	
t_r	Turn-On Rise Time			7.5	15	ns	
$t_{\text{d(off)}}$	Turn-Off Delay Time			25	40	ns	
t_f	Turn-Off Fall Time			5	10	ns	
Q_g	Total Gate Charge	$V_{\text{DS}} = 15 \text{ V}$, $I_D = 7.9 \text{ A}$, $V_{\text{GS}} = 5 \text{ V}$		9.5	13	nC	
Q_{gs}	Gate-Source Charge			3.3		nC	
Q_{gd}	Gate-Drain Charge			3.1		nC	
Drain-Source Diode Characteristics and Maximum Ratings							
I_s	Maximum Continuous Drain-Source Diode Forward Current			2.1		A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{\text{GS}} = 0 \text{ V}$, $I_s = 2.1 \text{ A}$ (Note 2)		0.7	1.2	V	
t_{rr}	Diode Reverse Recovery Time	$I_F = 7.9 \text{ A}$, $dI_F/dt = 100 \text{ A}/\mu\text{s}$		22		nS	
Q_{rr}	Diode Reverse Recovery Charge			20		nC	
Notes :							
1. R_{thJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{thJC} is guaranteed by design while R_{thCA} is determined by the user's board design.							
 <p>a) $50^\circ\text{C}/\text{W}$ when mounted on a 1 in^2 pad of 2 oz copper</p> <p>b) $105^\circ\text{C}/\text{W}$ when mounted on a 0.04 in^2 pad of 2 oz copper</p> <p>c) $125^\circ\text{C}/\text{W}$ when mounted on a minimum pad.</p> <p>Scale 1 : 1 on letter size paper</p>							
2. Pulse Test: Pulse Width < $300\mu\text{s}$, Duty Cycle < 2.0%							

Typical Characteristics

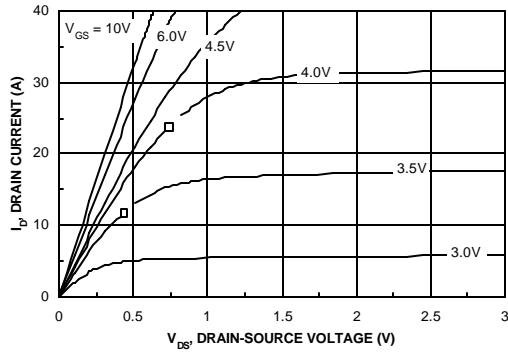


Figure 1. On-Region Characteristics.

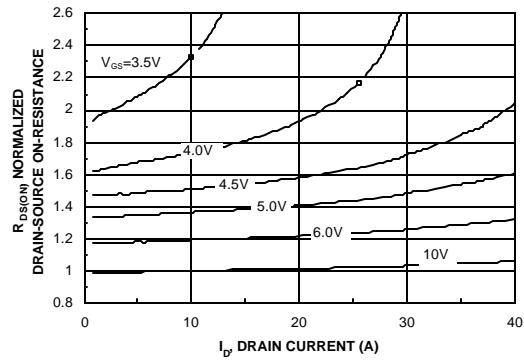


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

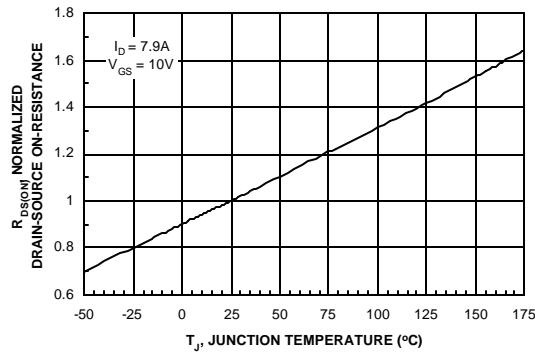


Figure 3. On-Resistance Variation with Temperature.

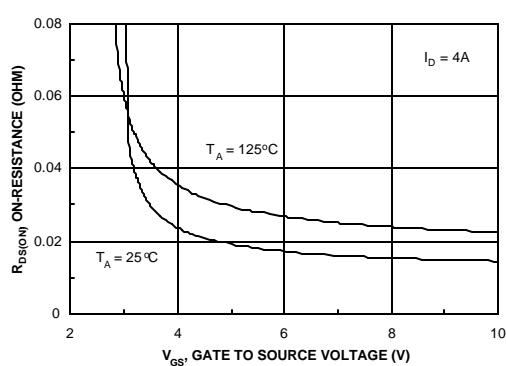


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

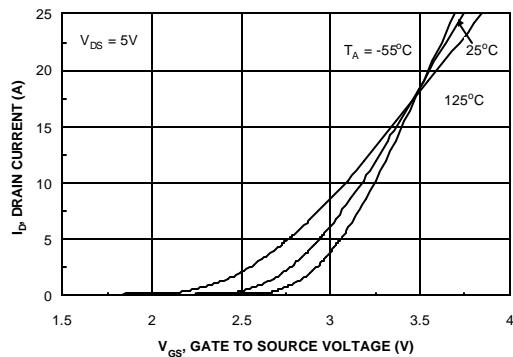


Figure 5. Transfer Characteristics.

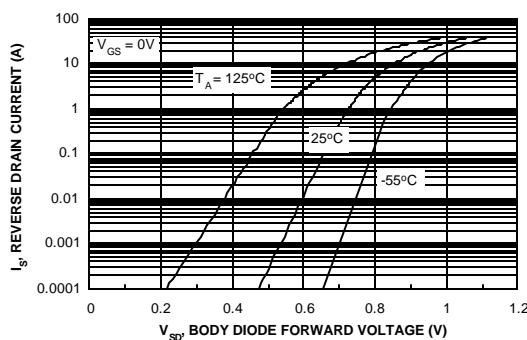


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

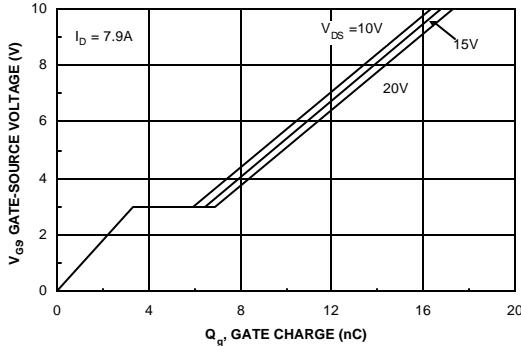


Figure 7. Gate Charge Characteristics.

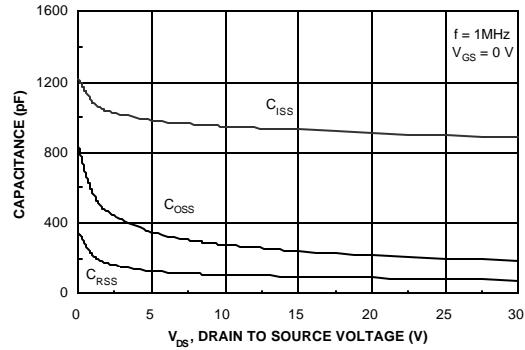


Figure 8. Capacitance Characteristics.

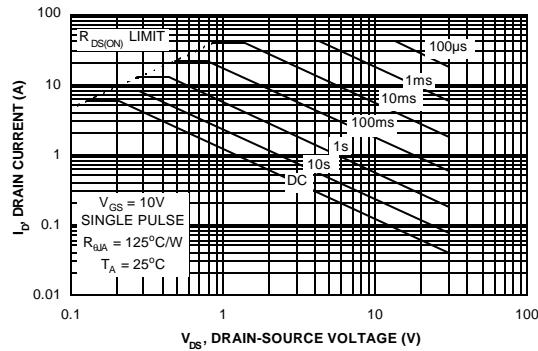


Figure 9. Maximum Safe Operating Area.

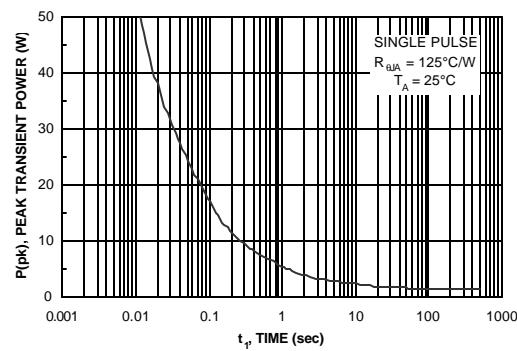


Figure 10. Single Pulse Maximum Power Dissipation.

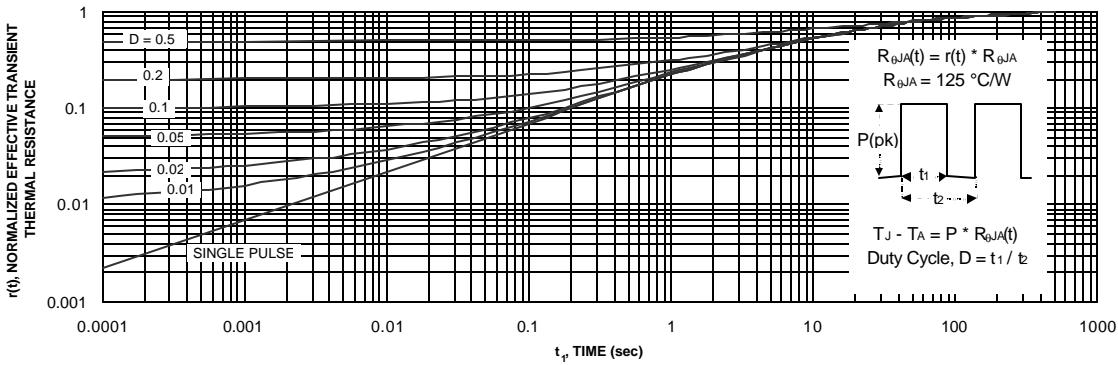


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c.
Transient thermal response will change depending on the circuit board design.

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